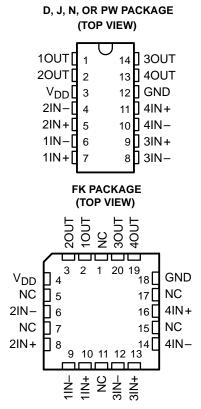
- Single- or Dual-Supply Operation
- Wide Range of Supply Voltages 2 V to 18 V
- Very Low Supply Current Drain 0.3 mA Typ at 5 V
- Fast Response Time . . . 200 ns Typ for TTL-Level Input Step
- Built-In ESD Protection
- High Input Impedance . . . $10^{12} \Omega$ Typ
- Extremely Low Input Bias Current 5 pA Typ
- Ultrastable Low Input Offset Voltage
- Input Offset Voltage Change at Worst-Case Input Conditions Typically 0.23 μV/Month, Including the First 30 Days
- Common-Mode Input Voltage Range Includes Ground
- Outputs Compatible With TTL, MOS, and CMOS
- Pin-Compatible With LM339

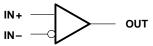
description

These quadruple differential comparators are fabricated using LinCMOSTM technology and consist of four independent voltage comparators designed to operate from a single power supply. Operation from dual supplies is also possible if the difference between the two supplies is 2 V to 18 V. Each device features extremely high input impedance (typically greater than $10^{12}~\Omega$), allowing direct interfacing with high-impedance sources. The outputs are n-channel open-drain configurations and can be connected to achieve positive-logic wired-AND relationships.



NC - No internal connection

symbol (each comparator)



The TLC374 has internal electrostatic discharge (ESD) protection circuits and has been classified with a 1000-V ESD rating using human body model testing. However, care should be exercised in handling this device as exposure to ESD may result in degradation of the device parametric performance.

The TLC374C is characterized for operation from 0°C to 70°C. The TLC374I is characterized for operation from -40° to 85°C. The TLC374M is characterized for operation over full military temperature range of -55°C to 125°C. The TLC374Q is characterized for operation from -40°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

LinCMOS is a trademark of Texas Instruments Incorporated.



TLC374, TLC374Q, TLC374Y LinCMOS™ QUADRUPLE DIFFERENTIAL COMPARATORS

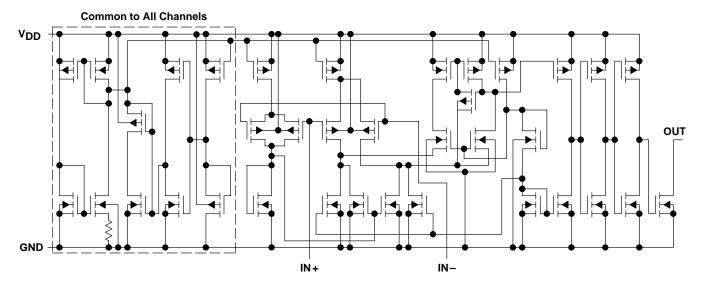
SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

AVAILABLE OPTIONS

	Via mov		PACI	KAGED DEVICES			CHIP
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	PLASTIC DIP (N)	TSSOP (PW)	FORM (Y)
0°C to 70°C	5 mV	TLC374CD	_	_	TLC374CN	TLC374CPW	TLC374Y
-40°C to 85°C	5 mV	TLC374ID	_	_	TLC374IN	_	_
−55°C to 125°C	5 mV	TLC374MD	TLC374MFK	TLC374MJ	TLC374MN	_	_
-40°C to 125°C	5 mV	TLC374QD	_	_	TLC374QN	_	_

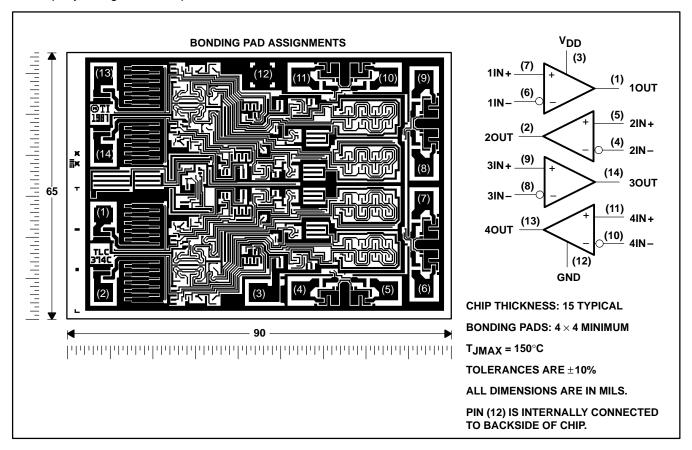
The D packages are available taped and reeled. Add R suffix to device type (e.g., TLC374CDR).

equivalent schematic (each comparator)



TLC374Y chip information

This chip, when properly assembled, displays characteristics similar to the TLC374C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



TLC374, TLC374Q, TLC374Y LinCMOS™ QUADRUPLE DIFFERENTIAL COMPARATORS

SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	18 V
Differential input voltage, V _{ID} (see Note 2)	
Input voltage, V _I	
Input voltage range, V _I	
Output voltage, VO	
Input current, I ₁	
Output current, I _O	20 mA
Duration of output short circuit to ground (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A : TLC374C	0°C to 70°C
TLC374I	40°C to 85°C
TLC374M	–55°C to 125°C
TLC374Q	
Storage temperature range, T _{stg}	65°C to 150°C
Case temperature range for 60 seconds: FK package	260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: D, N, or PW p	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: J package .	300°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values except differential voltages are with respect to network ground.
 - 2. Differential voltages are at IN+ with respect to IN -.
 - 3. Short circuits from outputs to V_{DD} can cause excessive heating and eventual device destruction.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	500 mW	7.6 mW/°C	84°C	500 mW	494 mW	190 mW
FK	500 mW	11.0 mW/°C	104°C	500 mW	500 mW	269 mW
J	500 mW	11.0 mW/°C	104°C	500 mW	500 mW	269 mW
N	500 mW	9.2 mW/°C	95°C	500 mW	500 mW	224 mW
PW	700 mW	5.6 mW/°C	_	448 mW	_	_

recommended operating conditions

		TLC	374C	TLC	374I	TLC3	74M	TLC3	374Q	UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{DD}		3	16	3	16	4	16	3	16	V
Common mode input voltage 1/1-	$V_{DD} = 5 V$	0	3.5	0	3.5	0	3.5	0	3.5	V
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	0	8.5	0	8.5	0	8.5	0	8.5	V
Operating free-air temperature, TA		0	70	-40	85	-55	125	-40	125	°C



electrical characteristics at specified free-air temperature, $V_{DD} = 5 \text{ V}$

	PARAMETER	TEST CON	DITIONS	.	TLC	374C		TLC	3741		TLC	374M		UNIT
	PARAMETER	TEST CON	DITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
\/.o	Input offset voltage	\/.	Soo Note 4	25°C		1	5		1	5		1	5	mV
VIO	input onset voltage	$V_{IC} = V_{ICR}min$	See Note 4	Full range			6.5			7			10	IIIV
1.0	Input offset current			25°C		1			1			1		pA
lio	input onset current			MAX			0.3			1			10	nA
l.D	Input bias current			25°C		5			5			5		pA
lΒ	input bias current			MAX			0.6			2			20	nA
\/	Common-mode input			25°C	0 to V _{DD} -1			0 to V _{DD} -1			0 to V _{DD} -1			V
VICR	voltage range		F		0 to V _{DD} -1.5			0 to V _{DD} -1.5			0 to V _{DD} -1.5			
1	High lovel output ourrent	\/ 1 \/	V _{OH} = 5 V	25°C		0.1			0.1			0.1		nA
ЮН	High-level output current	V _{ID} = 1 V	V _{OH} = 15 V	Full range			1			1			1	μΑ
\/a:	Low-level output voltage	V:= - 1 V	I _{OL} = 4 mA	25°C		150	400		150	400		150	400	mV
VOL	Low-level output voltage	$V_{ID} = -1 V$	IOL = 4 IIIA	Full range			700			700			700	IIIV
l _{OL}	Low-level output current	$V_{1D} = -1 V$,	V _{OL} = 1.5 V	25°C	6	16		6	16		6	16		mA
Inn	Supply current	V:p = 1 V	No load	25°C		300	600		300	600		300	600	
IDD	(four comparators)	$V_{ID} = 1 V$	INU IUAU	Full range			800			800			800	μΑ

[†] All characteristics are measured with zero common-mode input voltage unless otherwise noted. Full range is 0°C to 70°C for TLC374C, -40°C to 85°C for TLC374I, and -55°C to 125°C for the TLC374M, and -40°C to 125°C for TLC374Q. MAX is 70°C for TLC374C, 85°C TLC374I, and 125°C for the TLC374M, and 125°C for TLC374Q. IMPORTANT: See Parameter Measurement Information.

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, V_{DD} = 5 V, T_A = 25°C

PARAMETER	TEST (CONDITIONS	TLC37		UNIT	
		MIN	TYP	MAX		
Response time	R _L connected to 5 V through 5.1 k Ω ,	100-mV input step with 5-mV overdrive	650			ne
Response time	$C_L = 15 \text{ pF}^{\ddagger}$, See Note 5	TTL-level input step		200		ns

‡C_L includes probe and jig capacitance.

NOTE 5: The response time specified is the interval between the input step function and the instant when the output crosses 1.4 V.

LinCMOS™ QUADRUPLE DIFFERENTIAL COMPARATORS

TLC374, TLC374Q, TLC374Y LinCMOS™ QUADRUPLE DIFFERENTIAL COMPARATORS

SLCS118C - NOVEMBER 1983 - REVISED MARCH 1999

electrical characteristics at specified free-air temperature, V_{DD} = 5 V, T_A = 25°C (unless otherwise noted)

	PARAMETER	TEST CON	IDITIONS	TLC	374Y		UNIT
	PARAMETER	I EST CON	IDITIONS	MIN	TYP	MAX	UNII
VIO	Input offset voltage	$V_{IC} = V_{ICR}min,$	See Note 4		1	5	mV
IIO	Input offset current				1		pA
I _{IB}	Input bias current				5		pA
VICR	Common-mode input voltage range			0 to V _{DD} -1			V
ІОН	High-level output current	V _{ID} = 1 V,	V _{OH} = 5 V		0.1		nA
VOL	Low-level output voltage	$V_{ID} = -1 V$,	$I_{OL} = 4 \text{ mA}$		150	400	mV
loL	Low-level output current	$V_{ID} = -1 V$,	$V_{OL} = 1.5 \text{ mV}$	6	16		mA
I_{DD}	Supply current (four comparators)	V _{ID} =1 V,	No load		300	600	μΑ

NOTE 4: The offset voltage limits given are the maximum values required to drive the output above 4 V or below 400 mV with a 10-kΩ resistor between the output and V_{DD}. They can be verified by applying the limit value to the input and checking for the appropriate output state.

switching characteristics, $V_{DD} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

PARAMETER	TEST CO	ONDITIONS	Т	LC374Y		UNIT
PARAMETER	1231 C	CHOITIGHS	MIN	TYP	MAX	UNIT
Poononce time	R _L connected to 5 V through 5.1 k Ω ,	100-mV input step with 5-mV overdrive		650		20
Response time	$C_L = 15 \text{ pF}^{\dagger}$, See Note 5	TTL-level input step		200		ns

[†]C_L includes probe and jig capacitance.

NOTE 4: The response time specified is the interval between the input step function and the instant when the output crosses 1.4 V.



PARAMETER MEASUREMENT INFORMATION

The digital output stage of the TLC374 can be damaged if it is held in the linear region of the transfer curve. Conventional operational amplifier/comparator testing incorporates the use of a servo loop that is designed to force the device output to a level within this linear region. Since the servo-loop method of testing cannot be used, the following alternative for measuring parameters such as input offset voltage, common-mode rejection, etc., are offered.

To verify that the input offset voltage falls within the limits specified, the limit value is applied to the input as shown in Figure 1(a). With the noninverting input positive with respect to the inverting input, the output should be high. With the input polarity reversed, the output should be low.

A similar test can be made to verify the input offset voltage at the common-mode extremes. The supply voltages can be slewed as shown in Figure 1(b) for the V_{ICR} test, rather than changing the input voltages, to provide greater accuracy.

A close approximation of the input offset voltage can be obtained by using a binary search method to vary the differential input voltage while monitoring the output state. When the applied input voltage differential is equal, but opposite in polarity to the input offset voltage, the output changes state.

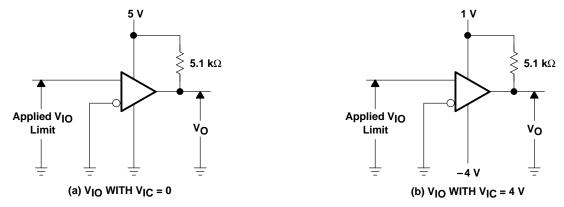


Figure 1. Method for Verifying That Input Offset Voltage is Within Specified Limits

PARAMETER MEASUREMENT INFORMATION

Figure 2 illustrates a practical circuit for direct dc measurement of input offset voltage that does not bias the comparator into the linear region. The circuit consists of a switching-mode servo loop in which U1a generates a triangular waveform of approximately 20-mV amplitude. U1b acts as a buffer with C2 and R4 removing any residual dc offset. The signal is then applied to the inverting input of the comparator under test, while the noninverting input is driven by the output of the integrator formed by U1c through the voltage divider formed by R9 and R10. The loop reaches a stable operating point when the output of the comparator under test has a duty cycle of exactly 50%, which can only occur when the incoming triangle wave is sliced symmetrically or when the voltage at the noninverting input exactly equals the input offset voltage.

Voltage divider R9 and R10 provide a step up of the input offset voltage by a factor of 100 to make measurement easier. The values of R5, R8, R9, and R10 can significantly influence the accuracy of the reading; therefore, it is suggested that their tolerance level be 1% or lower.

Measuring the extremely low values of input current requires isolation from all other sources of leakage current and compensation for the leakage of the test socket and board. With a good picoammeter, the socket and board leakage can be measured with no device in the socket. Subsequently, this open-socket leakage value can be subtracted from the measurement obtained with a device in the socket to obtain the actual input current of the device.

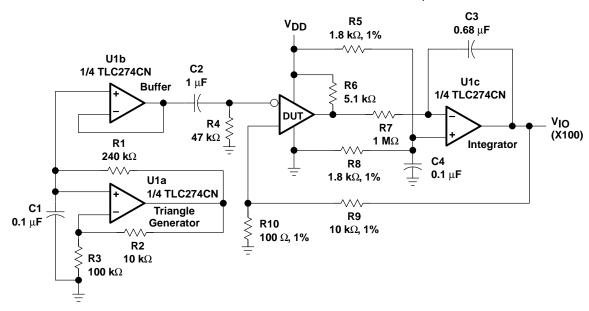
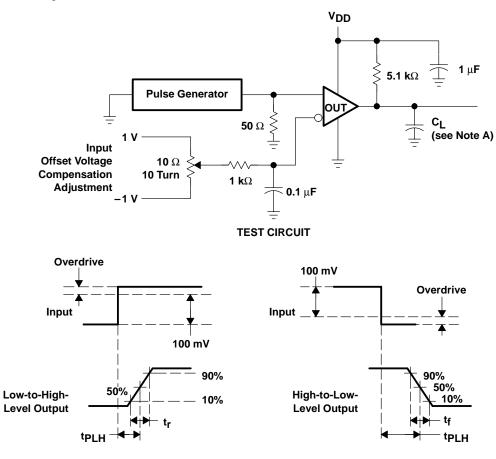


Figure 2. Test Circuit for Input Offset Voltage Measurement



PARAMETER MEASUREMENT INFORMATION

Response time is defined as the interval between the application of an input step function and the instant when the output reaches 50% of its maximum value. Response time, low-to-high-level output, is measured from the trailing edge of the input pulse. Response-time measurement at low input signal levels can be greatly affected by the input offset voltage. The offset voltage should be balanced by the adjustment at the inverting input (as shown in Figure 3) so that the circuit is just at the transition point. Then a low signal, for example, 105-mV or 5-mV overdrive, causes the output to change state.



VOLTAGE WAVEFORMS

NOTE A: C1 includes probe and jig capacitance.

Figure 3. Response, Rise, and Fall Times Test Circuit and Voltage Waveforms

PRINCIPLES OF OPERATION

LinCMOS process

LinCMOS process is a linear polysilicon-gate complimentary-MOS process. Primarily designed for single-supply applications, LinCMOS products facilitate the design of a wide range of high-performance analog functions from operational amplifiers to complex mixed-mode converters.

While digital designers are experienced with CMOS, MOS technologies are relatively new for analog designers. This short guide is intended to answer the most frequently asked questions related to the quality and reliability of LinCMOS products. Further questions should be directed to the nearest TI field sales office.

electrostatic discharge

CMOS circuits are prone to gate oxide breakdown when exposed to high voltages even if the exposure is only for very short periods of time. Electrostatic discharge (ESD) is one of the most common causes of damage to CMOS devices. It can occur when a device is handled without proper consideration for environmental electrostatic charges, e.g. during board assembly. If a circuit in which one amplifier from a dual operational amplifier is being used and the unused pins are left open, high voltages tends to develop. If there is no provision for ESD protection, these voltages may eventually punch through the gate oxide and cause the device to fail. To prevent voltage buildup, each pin is protected by internal circuitry.

Standard ESD-protection circuits safely shunt the ESD current by providing a mechanism whereby one or more transistors break down at voltages higher than normal operating voltages but lower than the breakdown voltage of the input gate. This type of protection scheme is limited by leakage currents which flow through the shunting transistors during normal operation after an ESD voltage has occurred. Although these currents are small, on the order of tens of nanoamps, CMOS amplifiers are often specified to draw input currents as low as tens of picoamps.

To overcome this limitation, TI design engineers developed the patented ESD-protection circuit shown in Figure 4. This circuit can withstand several successive 1-kV ESD pulses, while reducing or eliminating leakage currents that may be drawn through the input pins. A more detailed discussion of the operation of TI's ESD-protection circuit is presented on the next page.

All input an output pins of LinCMOS and Advanced LinCMOS products have associated ESD-protection circuitry that undergoes qualification testing to withstand 1000 V discharged from a 100-pF capacitor through a 1500- Ω resistor (human body model) and 200 V from a 100-pF capacitor with no current-limiting resistor (charged device model). These tests simulate both operator and machine handling of devices during normal test and assembly operations.

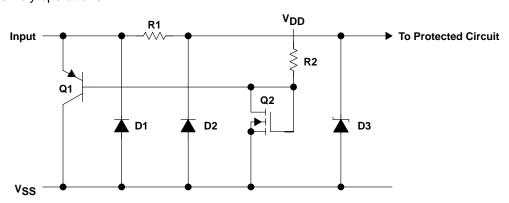


Figure 4. LinCMOS ESD-Protection Schematic



PRINCIPLES OF OPERATION

Input protection circuit operation

Texas Instruments patented protection circuitry allows for both positive- and negative-going ESD transients. These transients are characterized by extremely fast rise times and usually low energies, and can occur both when the device has all pins open and when it is installed in a circuit.

positive ESD transients

Initial positive charged energy is shunted through Q1 to V_{SS} . Q1 turns on when the voltage at the input rises above the voltage on V_{DD} by a value equal to the V_{EB} of Q1. The base current increases through R2 with input current as Q1 saturates. The base current through R2 as Q1 saturates forces the voltage at the drain and gate of Q2 to exceed its threshold level ($V_T \sim$ 22 to 26 V) and turn on Q2. The shunted input current through Q1 to V_{SS} is now shunted through the n-channel enhancement-type MOSFET Q2 to V_{SS} . If the voltage on the input pin continues to rise, the breakdown voltage of d3 is exceeded and all remaining energy is dissipated in R1 and D3. The breakdown voltage of D3 is designed to be 24 V to 27 V, which is well below the gate oxide voltage of the circuit to be protected.

negative ESD transients

The negative charged ESD transients are shunted directly through D1. Additional energy is dissipated in R1 and D2 as D2 becomes forward-biased. The voltage seen by the protected circuit is -0.3 V to -1 V (the forward voltage of D1 and D2).

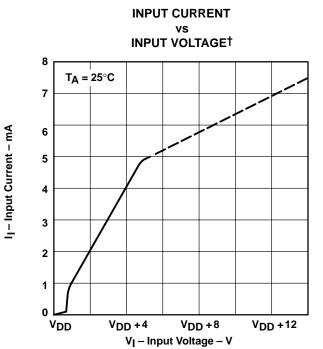
circuit-design considerations

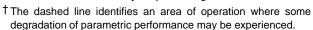
LinCMOS products are being used in actual circuits environments that have input voltages that exceed the recommended common-mode input voltage range and activate the input protection circuit. Even under normal operation, these conditions occur during circuit power up or power down, and in many cases, when the device is being used for a signal conditioning function. The input voltages can exceed V_{ICR} and not damage the device only if the inputs are current limited. The recommended current limit shown on most product data sheets is ± 5 mA. Figures 5 and 6 show typical characteristics for input voltage vs input current.

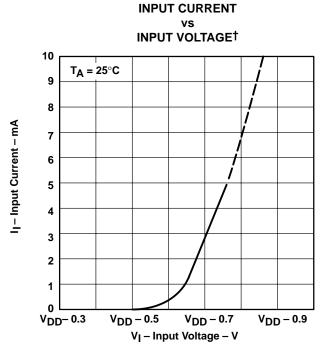
Normal operation and correct output state can be expected even when the input voltage exceeds the positive supply voltage. The input current should be externally limited even through internal positive current limiting is achieved in the input protection circuit by the action of Q1. When Q1 is on, it saturates and limits the current to approximately 5-mA collector current by design. When saturated, Q1 base current increases with input current. This current is forced into the V_{DD} pin and into the device I_{DD} or the V_{DD} supply through R2 producing the current limiting effects shown in Figure 5. This internal limiting lasts only as long as the input voltage is below the V_{T} of Q2.

When the input voltage exceeds the negative supply voltage, normal operation is affected and output voltage states may not be correct. Also, the isolation between channels of multiple devices (duals and quads) can be severely affected. External current limiting must be used since this current is directly shunted by D1 and D2, and no internal limiting is achieved. If normal output voltage states are required, an external input voltage clamp is required (see Figure 7).

PRINCIPLES OF OPERATION

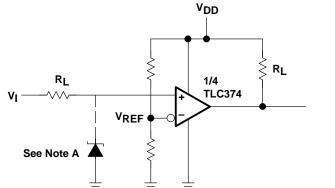






[†]The dashed line identifies an area of operation where some degradation of parametric performance may be experienced.

Figure 5 Figure 6



Positive Voltage Input Current Limit:

$$R_{I} = \frac{+V_{I} - V_{DD} - 0.3 V}{5 \text{ mA}}$$

Negative Voltage Input Current Limit:

$$R_{I} = \frac{-V_{I} - V_{DD} - (0.3 \text{ V})}{5 \text{ mA}}$$

NOTE A: If the correct output state is required when the negative input exceeds VSS, a Schotty clamp is required.

Figure 7. Typical Input Current-Limiting Configuration for a LinCMOS Comparator



2-Apr-2011

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
5962-87659012A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	
5962-8765901CA	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	
TLC374CD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC374CN-A	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC374CN-AE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC374CNE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC374CNSR	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CNSRG4	ACTIVE	SO	NS	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CPWLE	OBSOLETE	TSSOP	PW	14		TBD	Call TI	Call TI	
TLC374CPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374CPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	



PACKAGE OPTION ADDENDUM

Texas Instruments www.ti.com 2-Apr-2011

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TLC374IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374IN	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC374INE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	
TLC374MD	ACTIVE	SOIC	D	14	50	TBD	CU NIPDAU	Level-1-220C-UNLIM	
TLC374MDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TLC374MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type	
TLC374MJ	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	
TLC374MJB	ACTIVE	CDIP	J	14	1	TBD	A42	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures. TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.





ww.ti.com 2-Apr-2011

OTHER QUALIFIED VERSIONS OF TLC374, TLC374M:

• Military: TLC374M

NOTE: Qualified Version Definitions:

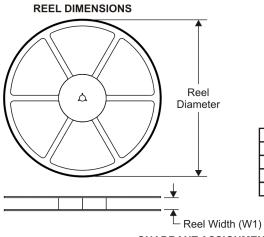
Catalog - TI's standard catalog product

• Military - QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

www.ti.com 19-Aug-2010

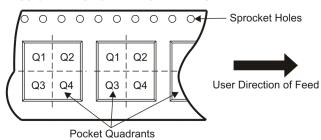
TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLC374CDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
TLC374CNSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
TLC374CPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TLC374IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

www.ti.com 19-Aug-2010



*All dimensions are nominal

7 III dillionorio di Chiannia								
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
TLC374CDR	SOIC	D	14	2500	333.2	345.9	28.6	
TLC374CNSR	SO	NS	14	2000	346.0	346.0	33.0	
TLC374CPWR	TSSOP	PW	14	2000	346.0	346.0	29.0	
TLC374IDR	SOIC	D	14	2500	346.0	346.0	33.0	

14 LEADS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

28 TERMINAL SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
 - Sody length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Audio	www.ti.com/audio	Communications and Telecom	www.ti.com/communications
Amplifiers	amplifier.ti.com	Computers and Peripherals	www.ti.com/computers
Data Converters	dataconverter.ti.com	Consumer Electronics	www.ti.com/consumer-apps
DLP® Products	www.dlp.com	Energy and Lighting	www.ti.com/energy
DSP	dsp.ti.com	Industrial	www.ti.com/industrial
Clocks and Timers	www.ti.com/clocks	Medical	www.ti.com/medical
Interface	interface.ti.com	Security	www.ti.com/security
Logic	logic.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Power Mgmt	power.ti.com	Transportation and Automotive	www.ti.com/automotive
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com	Wireless	www.ti.com/wireless-apps
RF/IF and ZigBee® Solutions	www.ti.com/lprf		

TI E2E Community Home Page

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2011, Texas Instruments Incorporated

e2e.ti.com